

11. Repetition

- What are the main sources of scattering in solids?
- Explain why phonons contribute differently to electrical and thermal conductivity in intermediate temperature ranges.
- Explain we can use magnetoresistance to map out the topology of the Fermi surface
- What are Landau tubes? How do they form?
- Explain quantum oscillations.

12. Cyclotron Frequency

If the magnetic field is applied in the z direction, the cyclotron effective mass is defined as:

$$m^* = \left(\frac{\det|\vec{m}|}{m_{zz}} \right)^{1/2}$$

Where \vec{m} is the effective mass tensor defined as $\vec{m}_{ij} = \left(\frac{1}{\hbar^2} \frac{\partial^2 E}{\partial k_i \partial k_j} \right)^{-1}$.

Calculate the cyclotron frequency for electrons at the Fermi surface in a nearly empty tight-binding band, described by:

$$E = -(E_1 \cos k_x a + E_2 \cos k_y b + E_3 \cos k_z c),$$

And show that the result indeed corresponds to the cyclotron frequency of free electrons of mass m^* .

13. de Haas-van Alphen effect

We have seen in the lecture that the measurement of the magnetic susceptibility $\chi = \mu_0 \partial M / \partial B$ shows, of clean metals and at sufficiently low temperatures, an oscillatory behavior as function of the applied magnetic field. These oscillations are periodic in $1/B$, and this effect is called the de Haas-van Alphen-Effect. The origin of the effect is rooted in the formation of Landau tubes and the associated changes of quantization conditions under field.

- Consider nearly free electron carriers of effective mass m^* in a cubic crystal of volume V in an homogeneous magnetic field B along the z direction. The energy dispersion now depends on two quantum numbers, the Landau tube index ν and the crystal momentum

along the field direction k_z so that it can be written: $E_v(k_z) = \frac{\hbar^2}{2m^*}k_z^2 + \hbar\omega_c^* \left(v + \frac{1}{2}\right)$ where $\omega_c^* = \frac{eB}{m^*}$ is the cyclotron frequency.

Use this to and show that the density of states $D(E)$ in a magnetic field B can be written as:

$$D(E) = \frac{V}{(2\pi)^2} \sqrt{\left(\frac{2m^*}{\hbar^2}\right)^3} \sum_{v=0}^{n_{max}} \frac{\hbar\omega_c^*}{\sqrt{E - \left(v + \frac{1}{2}\right) \hbar\omega_c^*}}$$

where n_{max} the number of Landau cylinders with states of energies less than E .

[Hint: this amounts to estimate the DOS for a collection of 1D systems]

- b) For $E_F \gg \hbar\omega_c^*$ show that $D(E_F)$ has periodic discontinuities as function of $1/B$.
- c) Calculate the period $\Delta(1/B)$ which can be expected for the de Haas-van Alphen effect in Potassium (treat the electrons as free in this case, that is $m^* = m$). Potassium (electronic structure: $[\text{Ar}]4s^1$) crystallizes in a body centered cubic unit cell with lattice constant $a = 5.225 \text{ \AA}$.